



SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

SOD-123 封装二极管/SOD-123 Plastic-Encapsulate Diodes

B5817W/B5818W/B5819W (SCHOTTKY DIODES)

特点/Features :

正向导通电压低 ;

用途/Applications :

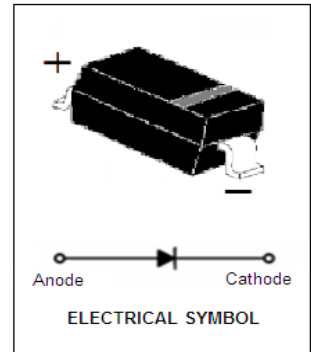
低压、高频等保护电路。

印章/ Marking:

B5817W: **SJ**

B5818W: **SK**

B5819W: **SL**



极限参数/Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	B5817W	B5818W	B5819W	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	20	30	40	
Peak Repetitive Peak Reverse Voltage	V_{RRM}				
Working Peak	V_{RWM}	20	30	40	V
DC Blocking Voltage	V_R				
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	V
Average rectified output current	I_O		1		A
Peak Forward Surge Current (@t≤8.3mS)	I_{FSM}		9		A
Repetitive Peak Forward Current	I_{FRM}		1.5		A
Power Dissipation	P_d		500		mW
Thermal Resistance Junction To Ambient	$R_{\theta JA}$		200		°C/mW
Storage Temperature	Tstg		-55~150		°C

电性能参数/Electrical characteristics (Ta=25°C)

参数/Parameter	符号	测试条件	最小值	典型值	最大值	单位
Reverse Breakdown Voltage B5817W B5818W B5819W	$V_{(BR)}$	$I_R=1mA$	20 30 40			V
Forward Voltage	V_F	$I_F=1A$ B5817W B5818W B5819W			0.45 0.55 0.6	V
		$I_F=3A$ B5817W B5818W B5819W			0.75 0.875 0.9	V
Reverse voltage leakage current B5817W B5818W B5819W	I_R	$V_R=20V$ $V_R=30V$ $V_R=40V$			1	mA
Diode Capacitance	C_D	$V_R=4V, f=1.0MHz$			120	pF



典型特性曲线图/Typical Characteristics

